IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Title: HIGH-QUALITY PRASEODYMIUM GATE DIELECTRICS (As Amended)

1303.033US2 Docket No.:

Filed: January 27, 2004

Examiner: Asok K Sarkar

MS Amendment

Serial No.: 10/765,619

Due Date: N/A

Group Art Unit: 2891

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

X A return postcard.

A Supplemental Information Disclosure Statement (2 pgs.), Form 1449 (3 pgs.), and copies of 10 cited documents.

X Communication Concerning Related Applications (1 page).

If not provided for in a separate paper filed herewith, Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

Customer Number 21186

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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this Aday of July, 2005.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

(GENERAL)

S/N 10/765,619

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Kie Y. Ahn et al.

Examiner: Asok K. Sarkar

Serial No.:

10/765,619

Group Art Unit: 2891

Filed:

January 27, 2004

Docket: 1303.033US2

Title:

HIGH-QUALITY PRASEODYMIUM GATE DIELECTRICS (AS AMENDED)

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

Serial/Patent No.

Filing Date/Issue Date

Attorney Docket

Title

11/176738

July 7, 2005

1303.145US1

METAL-SUBSTITUTED TRANSISTOR

GATES

11/178914

July 11, 2005

1303.061US3

NANOLAMINATES OF HAFNIUM OXIDE AND ZIRCONIUM OXIDE

Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicants request that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.

Respectfully submitted,

KIE Y. AHN ET AL.

By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

P.O. Box 2938

Minneapolis, MN 55402

(612) 371-2157

Date do

Rv

David R. Cochran

Reg. No. 46,632

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Name

Signatur

<u>S/N 10/765,619</u> <u>PATENT</u>

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Kie Y. Ahn et al.

Examiner:

Asok K Sarkar

Serial No.:

10/765,619

Group Art Unit:

2891

Filed:

January 27, 2004

Docket:

1303.033US2

Title:

HIGH-QUALITY PRASEODYMIUM GATE DIELECTRICS (As Amended)

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Supplemental Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Supplemental Information Disclosure Statement considered.

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Serial No :10/765,619

Filing Date: January 27, 2004

Title: HIGH-QUALITY PRASEODYMIUM GATE DIELECTRICS (As Amended)

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The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

P.O. Box 2938

Minneapolis, MN 55402

(612) 371-2157

Date 18 July 2005

y _____

David R. Cochran Reg. No. 46,632

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 28 day of July, 2005.

Name

Kacia Lee

PTC/SB/08A(10-01)
Approved for use through 10/31/2002, OM8 651-0031
US Patent & Trademark Office: U.S. DEPARTMENT OF COMMERCE

der the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control num Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE **Application Number** 10/765,619 STATEMENT BY APPLICANT January 27, 2004 (Use as many sheets as necessary) Filing Date **First Named Inventor** Ahn, Kie 2891 **Group Art Unit Examiner Name** Sarkar, Asok Attorney Docket No: 1303.033US2 Sheet 1 of 3

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EXAMINER

PTO/SB/08A(10-01)
Approved for use through 10/31/2002. OMB 651-0031
US Patent & Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO INFORMATION DISCLOSURE	Complete if Known		
STATEMENT BY APPLICANT	Application Number	10/765,619 January 27, 2004	
(Use as many sheets as necessary)	Filing Date		
	First Named Inventor	Ahn, Kie	
	Group Art Unit	2891	
	Examiner Name	Sarkar, Asok	
Sheet 2 of 3	Attorney Docket No: 1303.033US2		

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EXAMINER

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US Patent & Trademark Office: US, DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO INFORMATION DISCLOSURE	Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number Compilete if Known		
STATEMENT BY APPLICANT (Use as many sheets as necessary)	Application Number	10/765,619	
	Filing Date	January 27, 2004	
	First Named Inventor	Ahn, Kie	
	Group Art Unit	2891	
	Examiner Name	Sarkar, Asok	
Sheet 3 of 3	Attorney Docket No: 1303.033US2		

	OTHER	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
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